

*B/* not deposited on the inner circumferential face of the projecting part of the dielectric ring 50, and the cathode 38 and target 48 do not short-circuit to the metal ring 52 (in other words there is no short-circuiting to the processing chamber 34).

**IN THE CLAIMS:**

Please amend claim 14 as follows:

*B/* 14. (Twice Amended) A high frequency sputtering device, comprising:  
a processing chamber;  
a high frequency power supply;  
a cathode inside the processing chamber, the cathode being electrically insulated from the processing chamber and connected to the high frequency power supply, the cathode extending only along a given axial extent of the processing chamber;  
a target mounted on a first side of the cathode; and  
a metal plate mounted in the processing chamber adjacent to the cathode but only in a location outside of the given axial extent of the cathode, the metal plate having an opening in a central portion thereof, wherein an outer circumferential edge of the metal plate is electrically grounded to the processing chamber;  
the metal plate is arranged so as to form a gap having a first portion between the metal plate and the cathode and a second portion between the metal plate and the target, wherein the gap is sufficiently narrow and sufficiently long so as to substantially prevent plasma from passing through the gap.

Please add the following new claims 27 and 28 as follows:

27. (New) The high frequency sputtering device as claimed in claim 14,  
wherein the gap includes:  
an axial component defined by a space extending axially between the metal plate  
and the target, the axial component having an axially extending length, and  
a radial component defined by a space extending radially between a first radial point  
defined by an inner circumferential surface of the metal plate and a second radial point  
defined by an outer circumferential surface of the cathode, the radial component having a  
radially extending length,  
wherein the radially extending length is 3 mm or greater.

28. (New) The high frequency sputtering device as claimed in claim 14,  
wherein the gap includes:  
an axial component defined by a space extending axially between the metal plate  
and the target, the axial component having an axially extending length, and  
a radial component defined by a space extending radially between a first radial point  
defined by an inner circumferential surface of the metal plate and a second radial point  
defined by an outer circumferential surface of the cathode, the radial component having a  
radially extending length,  
wherein the axially extending length and the radially extending length together is 3  
mm or greater.